B U C KApplication NoteScientific#IR3003

Accurate Determination of Film Thickness by Fast-Scanning IR

Problem

Semiconductor components are made primarily from sur face-doped substr ates of silicon, gallium a rsenide, me rcury-cadmium telluride, and other highly refractive metalloid materials. Special lenses and mirro rs usuall y h ave a specific coating to impart some required optical property (anti-glare, U V-blocking, c olorcorrection, etc).

Polymer f ilms use d in pa ckaging a nd manufacturing a re o ften ma de to ce rtain thickness specifications. These films can either be pure, sin gle-component plastics, copolymers, or multi-layer laminates. All of these products need their respective surfaces, coatings, or layers accurately measured for QC or R& D purpos es, but are too thin for direct physical me asurement and too difficult to measure with cross-sectional microscopy.

Principle

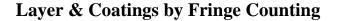
Place the sample in the *transmission* path of a beam of Infra-red energy and scan t he sample with a monochromator-based s ystem. The re will be some distortion of the IR light based on the interaction of a specific wavelength of IR energy and t he re fractive i ndex (and differential) of the sa mple/layer. This distortion creates a p attern known as fringing, and c an b e used to de termine film thicknesses from as small as 2 microns up to 2 millimeters! Since the accuracy of the fringing is dependent on the interaction of *individual* wavelengths of

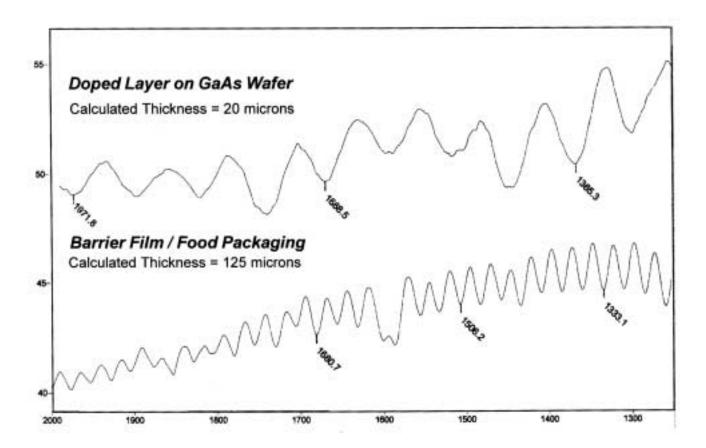
IR with the sample, the best da ta quality is obtained from a *scanning* based s ystem as opposed to an *interferometer* b ased desi gn, where all the energy is measured at once. Epitaxial layer and thin film thicknesses were a standard method for the old-style, double-beam dispersive instruments for several decades.

Practice

A magnetic film holder is placed in the sample compartment of the Buck Sc ientific M500 Scanning IR system. The sample is secur ed in place, perpendicular to the beam. Usi ng t he GRAMS®/AI soft ware package, a scan of t he sample is obta ined a nd the tr ansmission spectrum generated. Optiona 1 p rogrammed sequences in the so ftware will automatically pick the spectral range for a s eries of fringes, and then count the number of fringes within the region and c alculate the thickn ess based on refractive i ndex. A "m ean" t hickness c an be accurately det ermined b y calculating several areas of t he spectrum. A complete analytical cycle takes less than 5 minutes.

SIC: 222, 226, 227, 228, 229, 265, 267, 275, 307, 308, 382





The gallium arsenide wafer was run by transmission using a modified film holder and a "map" was made to verify the uniformity of the doping throughout the wafer. The barrier bag film was scanned using the magnetic film holder.

